

## APPENDIX B

The entire pending claims, including the "clean" version of the amended claims in this amendment, are as follows.

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18. (Twice Amended) An apparatus for depositing a layer on a substrate for a liquid crystal device, comprising:

a load lock chamber receiving a substrate having a gate wire pattern formed thereon;

a preheat chamber receiving the substrate from said load lock chamber and heating the substrate before deposition;

*F/* a deposition chamber depositing a gate insulating layer, an amorphous silicon layer and a doped amorphous silicon layer by chemical vapor deposition; and

a sputter chamber depositing a metal layer on the doped amorphous silicon layer by sputtering,

wherein the substrate is transferred from said deposition chamber to said sputter chamber in a vacuum, and

wherein said load lock chamber, said preheat chamber, said deposition chamber and said sputter chamber are arranged in series.

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22. / (Cancelled)

23. / (Cancelled)

24. / (Cancelled)

25. (Cancelled)

26. (Cancelled)

27. (Cancelled)

28. (Cancelled)

29. (Cancelled)

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30. (Amended) An apparatus for manufacturing a liquid crystal display, comprising:

a load lock chamber for receiving a substrate;

a preheat chamber for heating the substrate;

a first deposition chamber for depositing a gate insulating layer and an amorphous silicon

layer on the gate wire pattern;

a second deposition chamber for depositing a doped amorphous silicon layer on the  
substrate;

a sputter chamber for depositing a metal layer on the doped amorphous silicon layer; and

a vacuum passage for transferring the substrate in a vacuum from said deposition  
chamber to said sputter chamber to prevent oxidization of an upper surface of the doped  
amorphous silicon layer,

*F2  
Cont'd*  
wherein said load lock chamber, said preheat chamber, said first deposition chamber, said second deposition chamber, said vacuum passage and said sputter chamber are arranged in series.

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31. (Newly added) The deposition apparatus of claim 30, wherein the substrate has a gate wire pattern formed thereon.

32. (Cancelled)

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*F3*  
33. (Amended) The deposition apparatus of claim 30, wherein said first deposition chamber and said second deposition chamber are chemical vapor deposition (CVD) chambers.

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34. The deposition apparatus of claim 31, wherein the metal layer comprises chromium (Cr).

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*F4*  
35. (New) The deposition apparatus of claim 30, wherein the gate insulating layer is formed at a thickness between 3000 Å to 6000 Å, the amorphous silicon layer is formed at a thickness between 1000 Å to 3000 Å, and the doped amorphous silicon layer is formed at a thickness of 200 Å to 1000 Å.

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